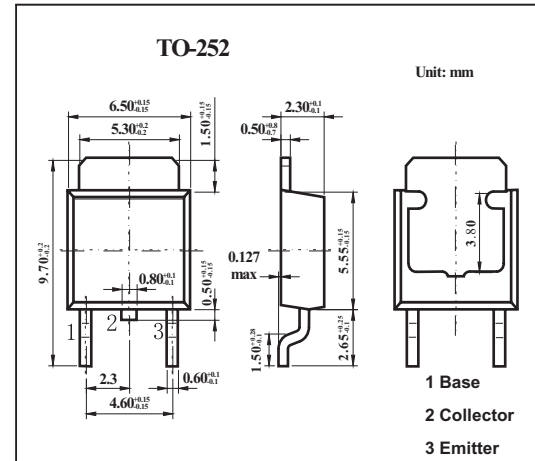


## AF Power Amplifier Applications

## 2SB1266



### ■ Features

- Suitable for sets whose height is restricted.
- High reliability.

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	-60	V
Collector-emitter voltage	$V_{CEO}$	-60	V
Emitter-base voltage	$V_{EBO}$	-6	V
Collector current	$I_C$	-3	A
Collector current (pulse)	$I_{CP}$	-8	A
Collector dissipation	$P_C$	1.65	W
$T_C = 25^\circ\text{C}$		30	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -40V, I_E = 0$			-100	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -4V, I_C = 0$			-100	$\mu\text{A}$
DC current Gain	$h_{FE}$	$V_{CE} = -5V, I_C = -0.5A$	70		280	
		$V_{CE} = -5V, I_C = -3A$	20			
Gain bandwidth product	$f_T$	$V_{CE} = -5V, I_C = -0.5A$		8		MHz
Output capacitance	$C_{ob}$	$V_{CB} = -10V, f = 1\text{MHz}$		60		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2A, I_B = -0.2A$		-0.4	-1	V
Base-emitter voltage	$V_{BE}$	$I_{CE} = -5V, I_C = -0.5A$		-0.7	-1	V
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1\text{mA}, I_E = 0$	-60			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -5\text{mA}, R_{BE} = \infty$	-60			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\text{mA}, I_C = 0$	-6			V

### ■ $h_{FE}$ Classification

Rank	Q	R	S
$h_{FE}$	70~140	100~200	140~280